



wafer

grown by MOCVD epitaxy on InP substrate. Provide FP and DFB epitaxial wafers with center wavelengths from 1250nm to 1650nm.

features:

center wavelength from 1250 to 1650nm

thickness error is controlled within 5%

doping concentration $1e17$ to $1e19$, the error is controlled within 20%
Material Defects Low
 $50cm^{-2}$ ($D > 10\mu m$)

application:

emitting laser

PD

high power laser